



# N-Channel Silicon MOSFET 2SK4098LS — General-Purpose Switching Device **Applications**

### Features

- · Low ON-resistance, low input capacitance, ultrahigh-speed switching.
- · Adoption of high reliability HVP process.
- Attachment workability is good by Mica-less package.
- · Avalanche resistance guarantee.

# **Specifications**

#### Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		600	V
Gate-to-Source Voltage	VGSS		±30	V
Drain Current (DC)	I <sub>Dc</sub> *1	Limited only by maximum temperature	7	А
	I <sub>Dpack</sub> *2	SANYO's ideal heat dissipation condition	6	А
Drain Current (Pulse)	IDP	PW≤10µs, duty cycle≤1%	28	А
Allowable Power Dissipation	D-		2.0	W
	PD	Tc=25°C (SANYO's ideal heat dissipation condition)	33	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C
Avalanche Energy (Single Pulse) *3	EAS		292	mJ
Avalanche Current *4	IAV		7	А

\*1 Shows chip capability

\*2 Package limited

\*3 VDD=99V, L=10mH, IAV=7A

\*4 L≤10mH, single pulse

Marking: K4098

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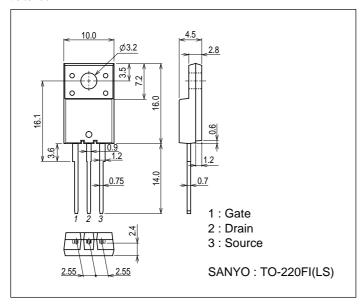
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## Electrical Characteristics at Ta=25°C

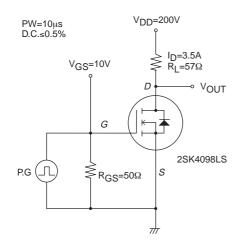
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=10mA, VGS=0V	600			V
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =480V, V <sub>GS</sub> =0V			1.0	mA
Gate-to-Source Leakage Current	IGSS	VGS=±30V, VDS=0V			±100	nA
Cutoff Voltage	VGS(off)	VDS=10V, ID=1mA	3		5	V
Forward Transfer Admittance	yfs	V <sub>DS</sub> =10V, I <sub>D</sub> =3.5A	2.1	4.2		S
Static Drain-to-Source On-State Resistance	RDS(on)	ID=3.5A, VGS=10V		0.9	1.1	Ω
Input Capacitance	Ciss	V <sub>DS</sub> =30V, f=1MHz		600		pF
Output Capacitance	Coss	V <sub>DS</sub> =30V, f=1MHz		120		pF
Reverse Transfer Capacitance	Crss	VDS=30V, f=1MHz		25		pF
Turn-ON Delay Time	t <sub>d</sub> (on)	See specified Test Circuit.		17		ns
Rise Time	tr	See specified Test Circuit.		34		ns
Turn-OFF Delay Time	td(off)	See specified Test Circuit.		80		ns
Fall Time	tf	See specified Test Circuit.		30		ns
Total Gate Charge	Qg	V <sub>DS</sub> =200V, V <sub>GS</sub> =10V, I <sub>D</sub> =7A		23.5		nC
Gate-to-Source Charge	Qgs	VDS=200V, VGS=10V, ID=7A		4.5		nC
Gate-to-Drain "Miller" Charge	Qgd	V <sub>DS</sub> =200V, V <sub>GS</sub> =10V, I <sub>D</sub> =7A		13.5		nC
Diode Forward Voltage	VSD	IS=7A, VGS=0V		0.9	1.2	V

### Package Dimensions

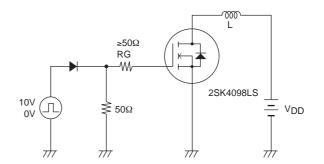
unit : mm (typ) 7509-002

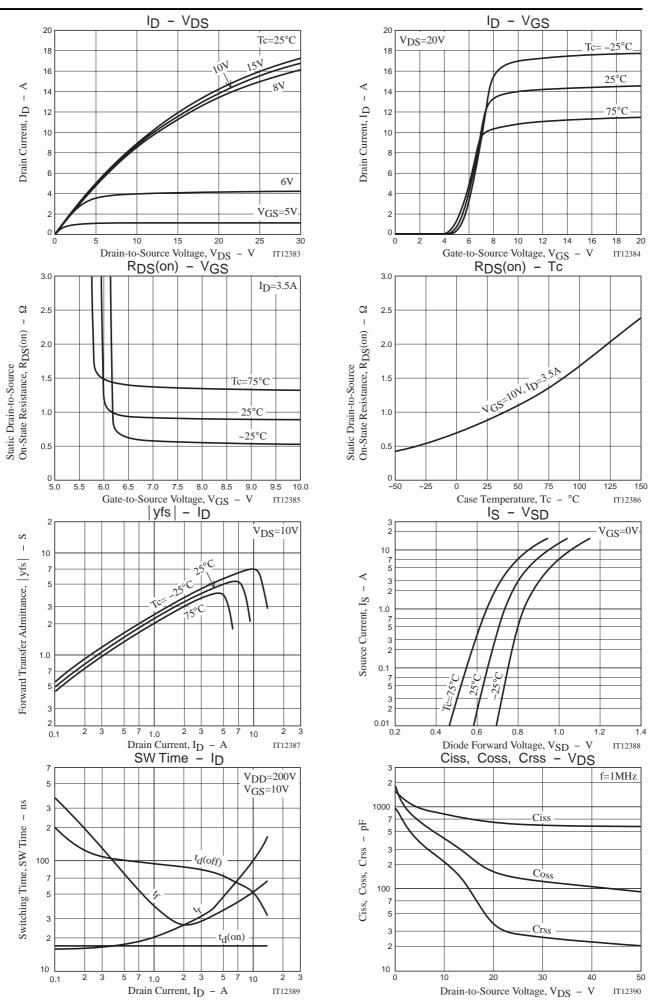


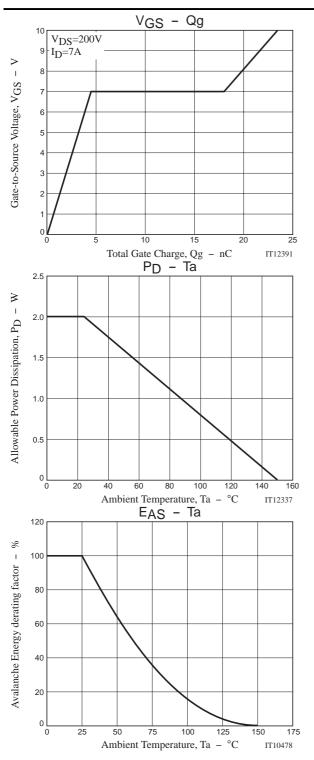
#### **Switching Time Test Circuit**

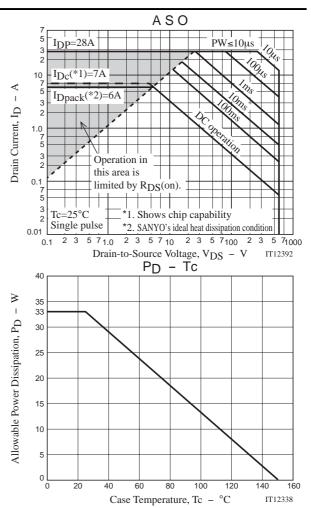


#### Avalanche Resistance Test Circuit









# Note on usage : Since the 2SK4098LS is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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